preliminary

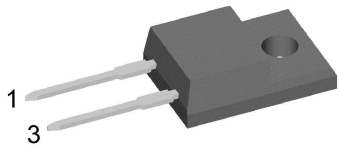
Schottky Diode Gen ²

V_{RRM}	=	45 V
I_{FAV}	=	10 A
V_F	=	0.52 V

High Performance Schottky Diode
Low Loss and Soft Recovery
Single Diode

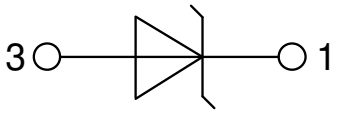
Part number

DSB10I45PM



Backside: isolated

E72873



Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-220FP

- Isolation Voltage: 2500 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Base plate: Plastic overmolded tab
- Reduced weight

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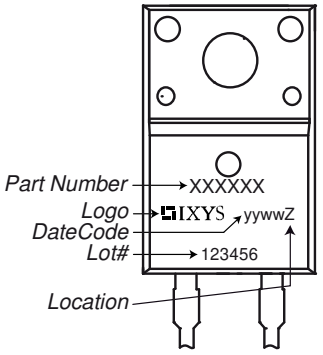
Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			45	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			45	V
I_R	*reverse current, drain current*	V_R = 45 V	T_{VJ} = 25°C			3.5	mA
		V_R = 45 V	T_{VJ} = 100°C			35	mA
V_F	*forward voltage drop*	I_F = 10 A	T_{VJ} = 25°C			0.56	V
		I_F = 20 A				0.78	V
		I_F = 10 A	T_{VJ} = 125°C			0.52	V
		I_F = 20 A				0.74	V
I_{FAV}	*average forward current*	T_C = 115°C	T_{VJ} = 150°C			10	A
		rectangular d = 0.5					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 150°C			0.30	V
r_F	*slope resistance* }					20.8	mΩ
R_{thJC}	*thermal resistance junction to case*					4.5	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.5		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			30	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine; V_R = 0 V	T_{VJ} = 45°C			260	A
C_J	*junction capacitance*	V_R = 5 V f = 1 MHz	T_{VJ} = 25°C		326		pF

preliminary

Package TO-220FP					**Ratings**			
Symbol	**Definition**	**Conditions**			**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal					35	A
T_{VJ}	*virtual junction temperature*				-55		150	°C
T_{op}	*operation temperature*				-55		125	°C
T_{stg}	*storage temperature*				-55		150	°C
Weight						2		g
M_D	*mounting torque*				0.4		0.6	Nm
F_C	*mounting force with clip*				20		60	N
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	3.2	2.7			mm
$d_{Spb/Apb}$			*terminal to backside*	2.5	2.5			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA		2500			V
		t = 1 minute			2100			V

Product Marking



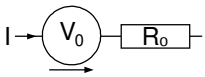
Part description

D = Diode
S = Schottky Diode
B = ultra low VF
10 = Current Rating [A]
I = Single Diode
45 = Reverse Voltage [V]
PM = TO-220ACFP (2)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSB10I45PM	DSB10I45PM	Tube	50	504423

Equivalent Circuits for Simulation

** on die level* T_{VJ} = 150°C



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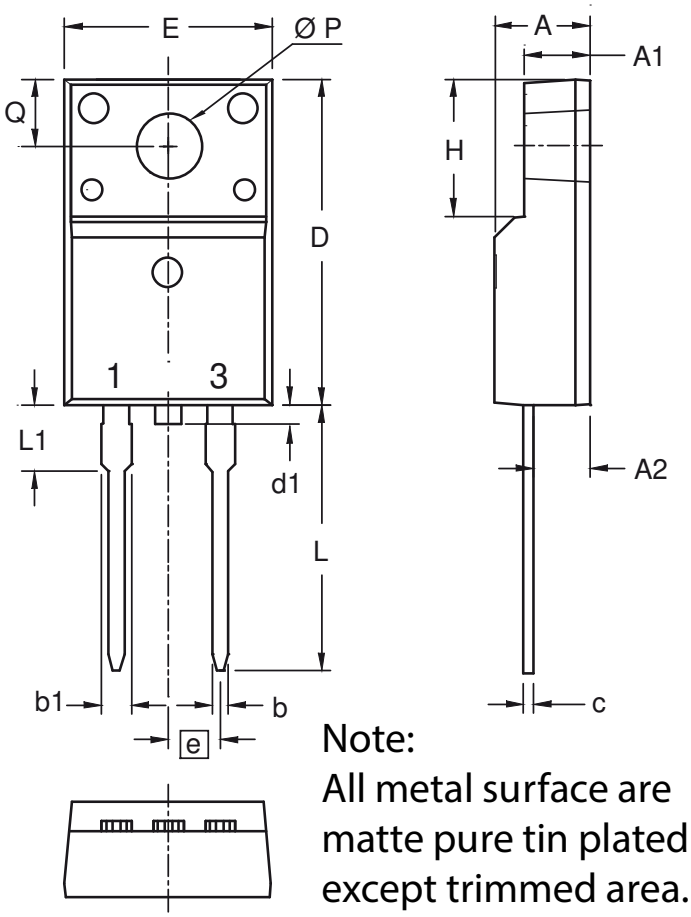
$V_{0\ max}$	*threshold voltage*	0.3	V
$R_{0\ max}$	*slope resistance **	17.7	mΩ

Outlines TO-220FP



Note:
All metal surface are matte pure tin plated except trimmed area.

Dim.	Millimeters		Inches	
	min	max	min	max
A	4.50	4.90	0.177	0.193
A1	2.34	2.74	0.092	0.108
A2	2.56	2.96	0.101	0.117
b	0.70	0.90	0.028	0.035
b1	1.27	1.47	0.050	0.058
c	0.45	0.60	0.018	0.024
D	15.67	16.07	0.617	0.633
d1	0	1.10	0	0.043
E	9.96	10.36	0.392	0.408
e	2.54 BSC		0.100 BSC	
H	6.48	6.88	0.255	0.271
L	12.68	13.28	0.499	0.523
L1	3.03	3.43	0.119	0.135
Ø P	3.08	3.28	0.121	0.129
Q	3.20	3.40	0.126	0.134